

### Tutorial 3

#### Exercise 1: Responsivity and quantum efficiency

1. Calculate the responsivity of a photodiode that has a quantum efficiency of 70% at a wavelength of 850 nm.
2. Propose a circuit that can measure the responsivity and quantum efficiency
3. Based on the last questions how can increase the quantum efficiency up to 85%.

Use the formulas bellow that apply generally for most common Photodiodes.

$$\text{Quantum Efficiency ratio } \eta = \frac{\text{Number of collected electrons}}{\text{Number of incident photons}}$$

$$\text{Responsivity } R = \frac{I_p}{P_{in}} = \frac{\text{Current output } (I_p)}{\text{Incident optical power } (P_{in})} = \frac{\eta \cdot q}{h \cdot \nu} = \frac{\eta \cdot q \cdot \lambda}{h \cdot c}$$

#### Exercise 2: Photoconductors and Gain

A specialized semiconductor material is used as a photoconductor. It has a carrier lifetime  $\tau = 10\mu s$  and an internal electron transit time  $\tau_{tr} = 100ns$ . The device is illuminated with a light source that provides a photon flux  $\Phi = 5 \times 10^{14} \text{photons/sec}$  and has a quantum efficiency  $\eta = 0.80$

1. If the carrier lifetime in a photoconductor is  $\tau = 10 \mu s$  and the electron transit time across the device is  $\tau_{tr} = 100 ns$ , what is the gain?
2. Why Photoconductors are unique?
3. Determine the primary photocurrent ( $I_p$ ):
4. Calculate the total current and analyze System Sensitivity if the transit time increase to  $400ns$
5. Propose a circuit to analyze the system sensitivity

We can use the formulas  $G = \frac{\tau}{\tau_{tr}}$  and  $I_p = q \cdot \eta \cdot \Phi \cdot G$

#### Exercise 3: Avalanche Photodiodes (APD)

1. An APD with a breakdown voltage of 100V is biased at 95V. If  $n = 3$ , what is the internal gain  $M$ ?
2. Explain the multiplication process in the APDs.
3. Recalculate the factor  $M$  for higher voltage 98V
4. Analyze the sensitivity performance

$$\text{We can use this formula Factor } M = \frac{I_{multiplied}}{I_{primary}} = \frac{1}{1 - \left(\frac{V_R}{V_{BR}}\right)^n}$$

$V_R$  is reverse bias,  $V_{BR}$  is breakdown voltage, and  $n$  is a material constant called Miller coefficient.

#### Exercise 4: Phototransistors

A phototransistor gain  $\beta = 150$ . If the light-generated base current is  $2\mu A$

1. Find the collector current (ignore dark current).
2. If we collect an actual  $I_C = 310\mu A$  what is the dark current value?
3. Propose a circuit to evaluate the consequences of a dark current

The phototransistor uses the transistor's common-emitter current gain  $\beta$  to amplify the base photocurrent:  $I_C = (\beta + 1) \cdot I_\lambda + I_{\text{dark}}$

$I_\lambda$  is the primary photocurrent generated at the base-collector junction

### Exercise 5: Smart Streetlight Sensor

A common-emitter phototransistor circuit is designed to trigger a logic high (5V) when it detects dusk.

1. Calculate the Primary Responsivity ( $R$ )
2. Calculate the Base Photocurrent ( $I_\lambda$ )
3. Calculate the Total Collector Current ( $I_C$ )
4. Calculate the Final Output Voltage ( $V_{out}$ )
5. Propose a circuit for this purpose

Data:  $\lambda = 600\text{nm}$ ;  $P_{in} = 10\mu W$ ;  $\eta = 65\%$ ;  $\beta = 120$ ; Load resistor  $R_L = 10K\Omega$ ;  $V_{CC} = 12V$  and  $I_{\text{dark}} = 50nA$